

Silicon PNP Power Transistors

2SA1074

DESCRIPTION

- With TO-3 package
- Excellent safe operating area

APPLICATIONS

- For high power audio ,stepping motor and other linear applications
- Relay or solenoid drivers
- DC-DC converters inverters

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

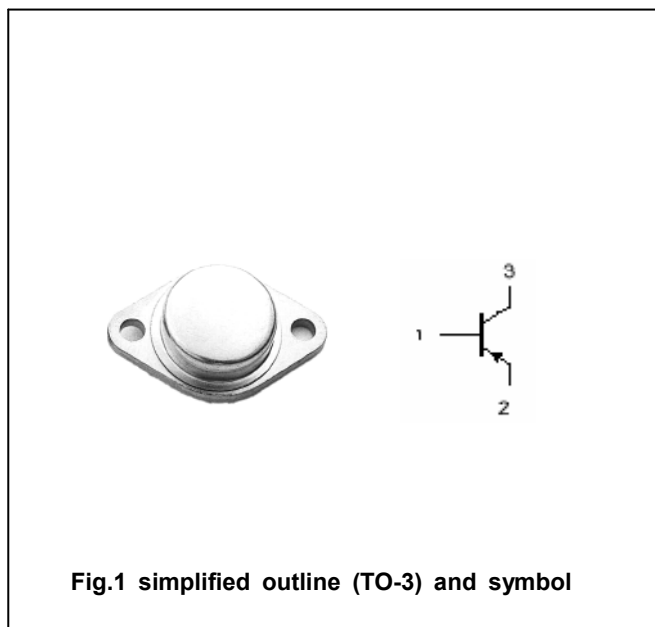


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-160	V
V _{CEO}	Collector-emitter voltage	Open base	-160	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-15	A
I _B	Base current		-7	A
P _C	Collector power dissipation	T _C =25□	150	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	0.98	□/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =-0.2A ; I _B =0	-160			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-4A ; I _B =-0.4A			-1.1	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-10A ; I _B =-3.3A			-3.0	V
V _{BE}	Base-emitter on voltage	I _C =-4A ; V _{CE} =-4V			-1.8	V
I _{CEO}	Collector cut-off current	V _{CE} =-60V ; V _{BE(off)} =0			-0.1	mA
I _{CEV}	Collector cut-off current	V _{CE} =Rated Value ; V _{BE(off)} =1.5V T _C =150°C			-1.0 -6.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V ; I _C =0			-0.1	mA
h _{FE-1}	DC current gain	I _C =-4A ; V _{CE} =-4V	20			
h _{FE-2}	DC current gain	I _C =-10A ; V _{CE} =-4V	5			

PACKAGE OUTLINE

